

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	SUD50N03-12P-GE3
Manufacturer:	Vishay Siliconix
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-siliconix/sud50n03-12p-ge3.html>

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Contact Information

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New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

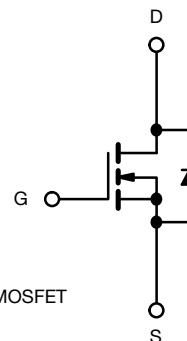
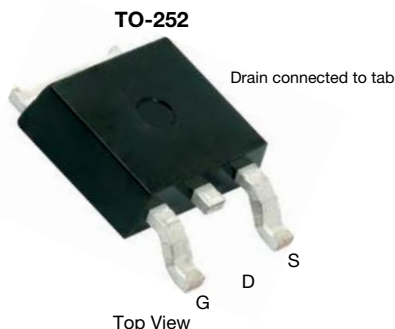
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a
30	0.0120 at $V_{GS} = 10$ V	16.8
	0.0175 at $V_{GS} = 4.5$ V	13.9

FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



Ordering Information:

SUD50N03-12P-GE3 (lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25$ °C	I_D	16.8	A
	$T_A = 100$ °C		10.6	
Pulsed Drain Current		I_{DM}	40	
Continuous Source Current (Diode Conduction) ^a		I_S	3.6	
Avalanche Current	$L = 0.1$ mH	I_{AS}	30	
Single Pulse Avalanche Energy		E_{AS}	45	mJ
Maximum Power Dissipation	$T_C = 25$ °C	P_D	39	W
	$T_A = 25$ °C		5.4 ^a	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	18	23	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	2.6	3.2	

Note

a. Surface mounted on FR4 board, $t \leq 10$ s.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. ^a	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	-	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 125 °C	-	-	50	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40	-	-	A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.0100	0.0120	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C	-	-	0.0170	
		V _{GS} = 4.5 V, I _D = 15 A	-	0.0138	0.0175	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	15	-	-	S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	1600	-	pF
Output Capacitance	C _{oss}		-	285	-	
Reverse Transfer Capacitance	C _{rss}		-	140	-	
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 50 A	-	28	42	nC
Gate-Source Charge ^c	Q _{gs}		-	6	-	
Gate-Drain Charge ^c	Q _{gd}		-	5	-	
Gate Resistance	R _g	f = 1 MHz	0.3	1.5	3.0	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.3 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω	-	9	15	ns
Rise Time ^c	t _r		-	15	25	
Turn-Off Delay Time ^c	t _{d(off)}		-	20	30	
Fall Time ^c	t _f		-	12	20	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)						
Pulsed Current	I _{SM}		-	-	100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 40 A, V _{GS} = 0 V	-	1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs	-	25	70	ns

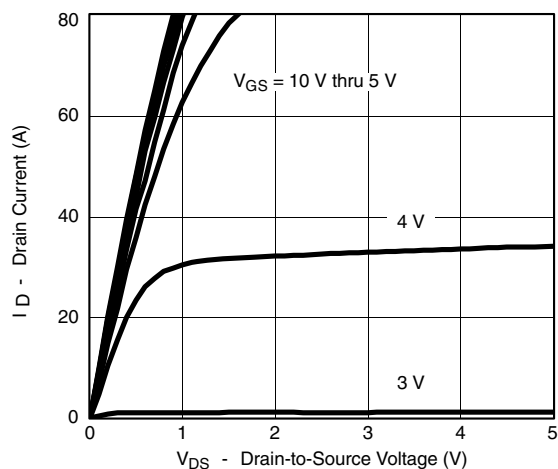
Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
c. Independent of operating temperature.

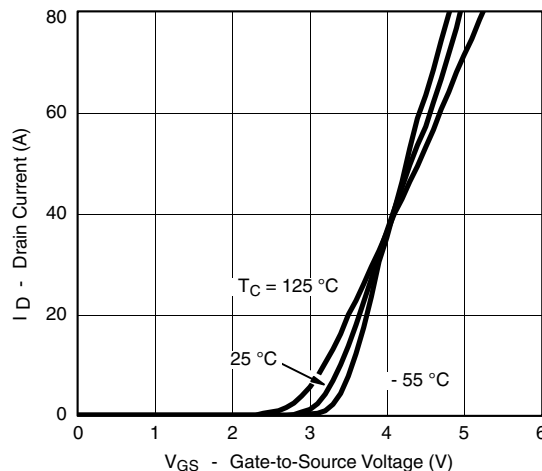
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



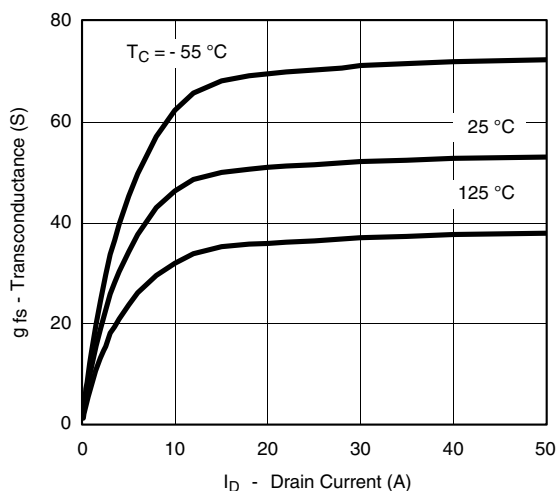
TYPICAL CHARACTERISTICS (25 °C unless noted)



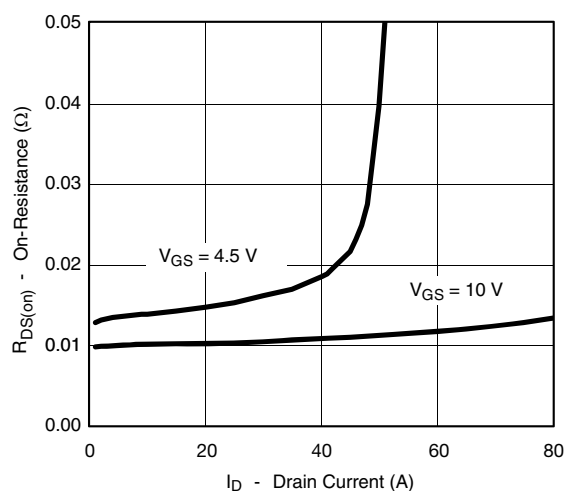
Output Characteristics



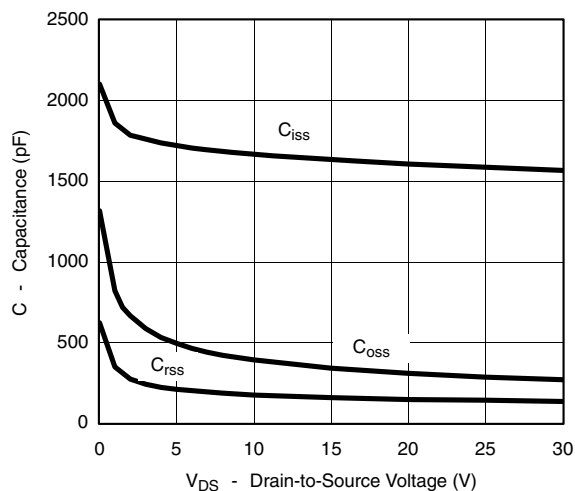
Transfer Characteristics



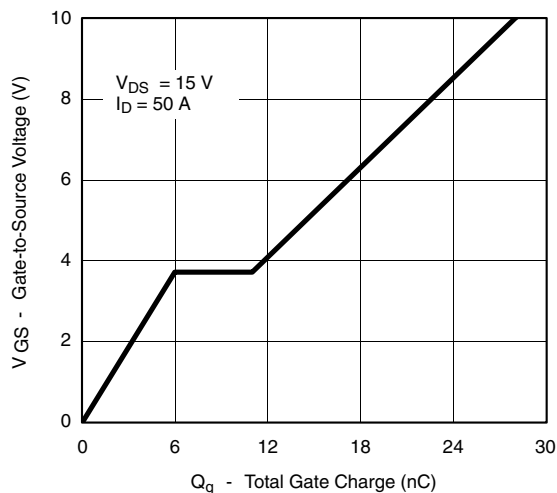
Transconductance



On-Resistance vs. Drain Current



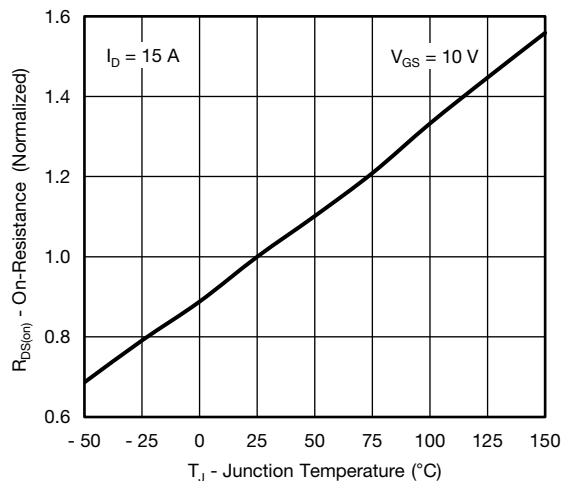
Capacitance



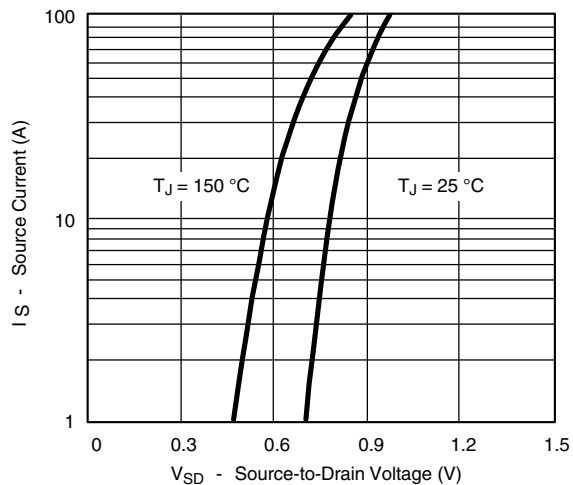
Gate Charge



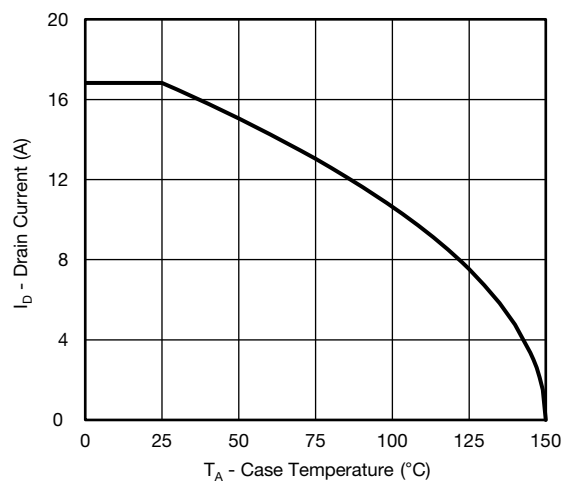
THERMAL RATINGS



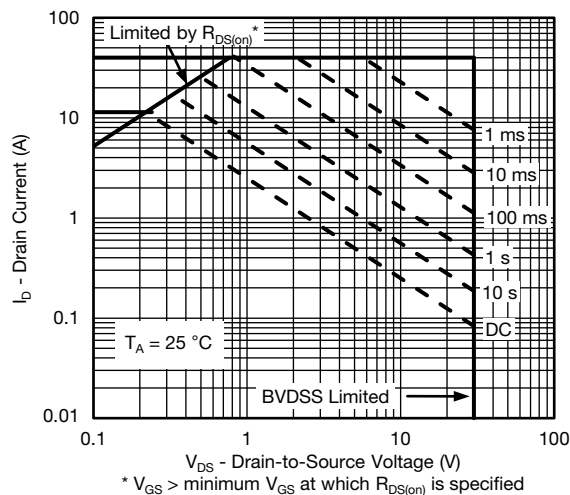
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



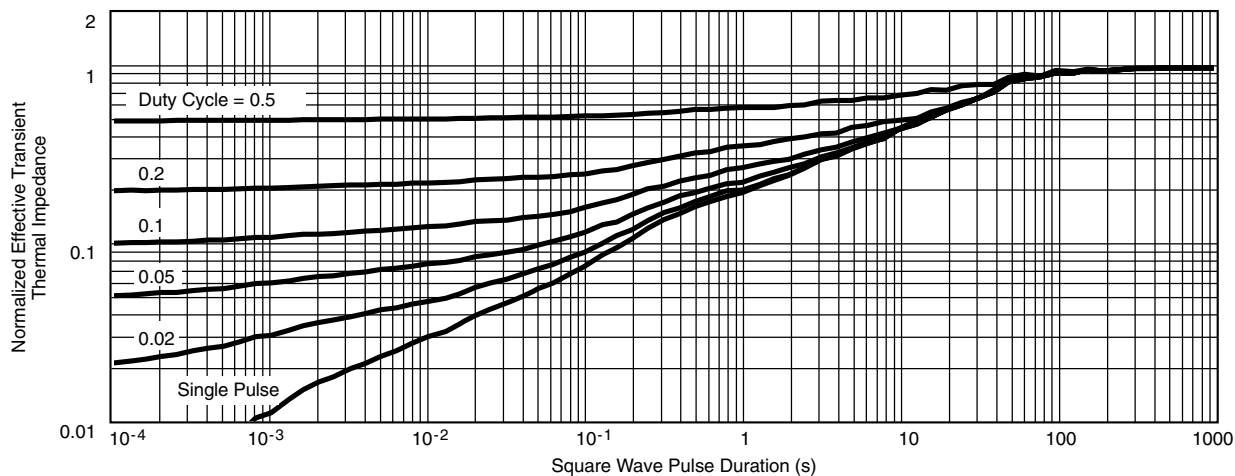
Maximum Drain Current vs. Ambient Temperature



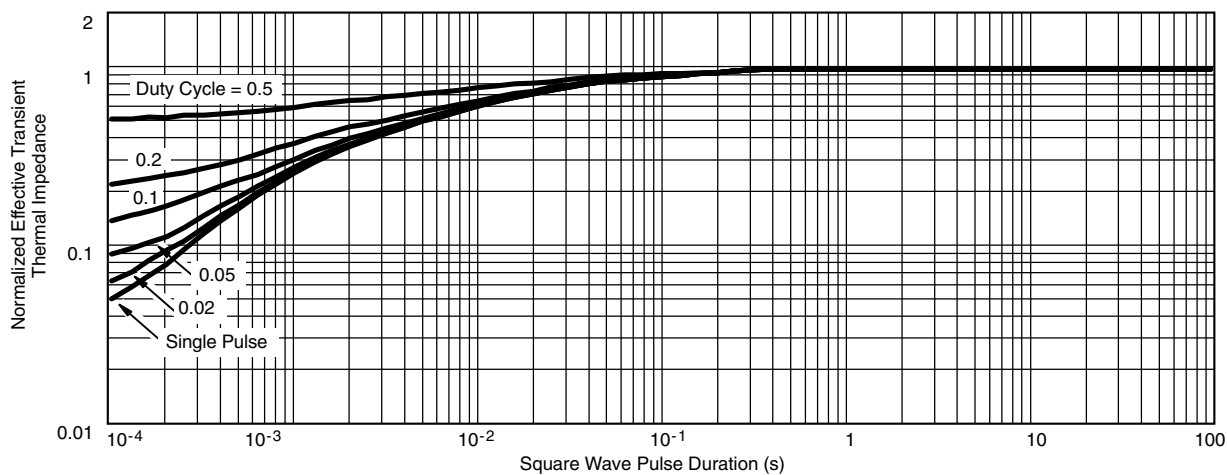
Safe Operating Area



THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Ambient

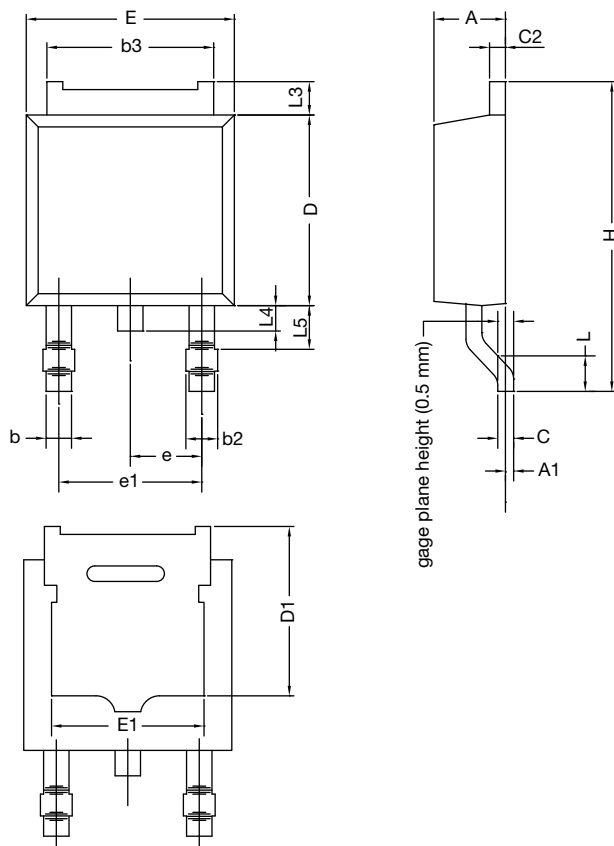


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67357.



TO-252AA Case Outline

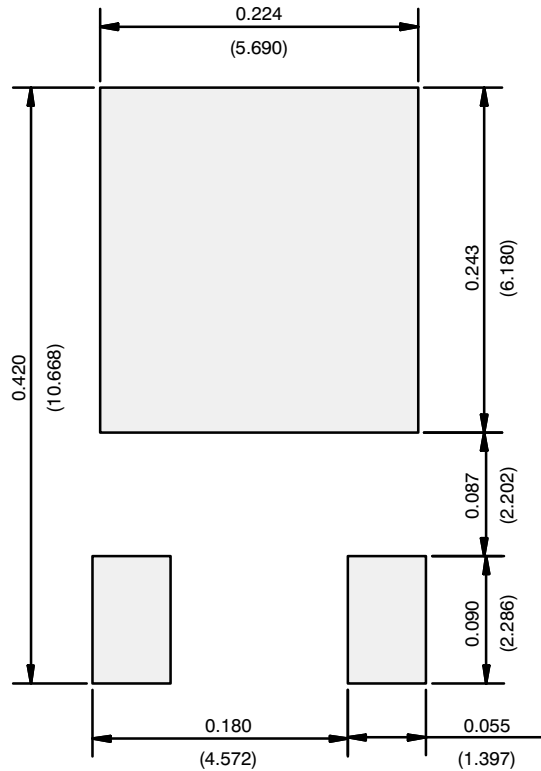


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347				

Notes

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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